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örney Docket No. 5649-919

**PATENT** 

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Chung et al.

U.S. Patent No.: 6,734,480

Application Serial No.: 10/047,706

Issued: May 11, 2004

Filed: January 15, 2002

Semiconductor Capacitors Having Tantalum Oxide Layers

Date: June 8, 2004

Certificate

JUN 1 5 2004

Commissioner for Patents P.O. Box 1450

of Correction

Alexandria, VA 22313-1450

## REQUEST FOR ENTRY OF CERTIFICATE OF CORRECTION UNDER 35 U.S.C §254 AND 37 C.F.R. §1.322

Sir:

The Assignee of record for the above-referenced patent hereby requests, pursuant to 35 U.S.C §254 and 37 C.F.R. §1.322, that a Certificate of Correction be issued. This request is made in order to correct the mistakes incurred through the fault of the U.S. Patent and Trademark Office. No fee is believed due. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

The mistakes appearing in the patent are set forth with corrections on the Certificate of Correction enclosed herewith, with an additional copy thereof and a return post card.

Respectfully submitted,

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Certificate of Mailing under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 8, 2004.

Katie Chung

## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

6,734,480

**DATED** 

May 11, 2004

INVENTOR(S)

Chung et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

## On the Cover Sheet:

Section 57, the Abstract, should read as follows:

Semiconductor capacitors comprise first electrodes, second electrodes, and tantalum oxide layers positioned between the first electrodes and the second electrodes. The tantalum oxide layers are formed by depositing at least one precursor and ozone gas, the at least one precursor represented by the formula:

$$\begin{array}{c|c} & \text{OCH}_2\text{CH}_3 \\ \text{H}_3\text{CH}_2\text{CO} & \text{Ta} & \text{CH}_2 \\ \text{H}_3\text{CH}_2\text{CO} & \text{X} & \text{CH}_2 \\ & \text{R}_2 & \text{R}_1 \end{array}$$

wherein X is selected from the group consisting of nitrogen, sulfur, oxygen, and a carbonyl group; and wherein R1 and R2 are independently alkyl.

MAILING ADDRESS OF SENDER: Myers, Bigel, Sibley & Sajovec P.O. Box 37428 Raleigh, NC 27627 PATENT NO. 6,734,480 No. of additional copies:

 $\Rightarrow$ 

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